



JCD16A065A

SiC Schottky Diode

Rev.1.1

DESCRIPTION

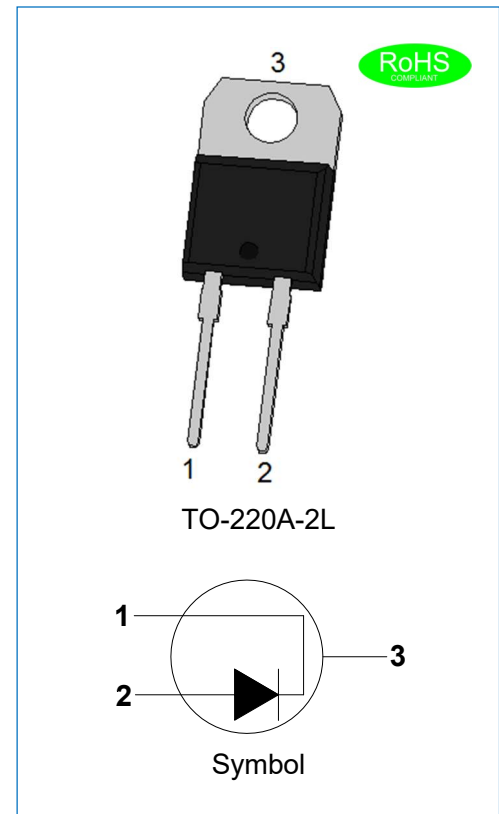
- ✧ 650V Schottky diode
- ✧ Zero reverse recovery current
- ✧ Zero forward recovery voltage
- ✧ High frequency operation
- ✧ Switching characteristics independent of temperature
- ✧ Fast switch
- ✧ Positive temperature coefficient of forward voltage (V_F)

BENEFIT

- ✧ Lower switching loss
- ✧ No thermal runaway in parallel devices
- ✧ Lower heatsink dependent
- ✧ Electrically isolated package
- ✧ Ceramic package provides 2500V isolation

APPLICATION

- ✧ Switch mode power supplies(SMPS)
- ✧ Boost diodes in PFC or DC/DC stages
- ✧ Free wheeling diodes in inverter stages
- ✧ AC/DC converters



ABSOLUTE MAXIMUM RATING (Rating at 25°C junction temperature unless otherwise specified.)

Parameter		Symbol	Value	Unit
Maximum repetitive peak reverse voltage		V_{RRM}	650	V
Maximum DC blocking voltage		V_{DC}	650	V
Average forward current	$T_C=150^{\circ}\text{C}$	$I_{F(AV)}$	16	A
Repetitive peak forward surge current	$t_P=10\text{ms}, T_C=25^{\circ}\text{C}$	I_{FRM}	105	A
Non-repetitive peak forward surge current	$t_P=10\text{ms}, T_C=25^{\circ}\text{C}$	I_{FSM}	135	A
Non-repetitive peak forward surge current	$T_C=25^{\circ}\text{C}, t_P=10\mu\text{s}, \text{Pulse}$	I_{FMax}	1200	A
Power dissipation	$T_C=25^{\circ}\text{C}$ $T_C=110^{\circ}\text{C}$	P_{tot}	205 89	W
Operating junction temperature range		T_j	-55 to+175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to+175	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS(Rating at 25°C junction temperature unless otherwise specified.)

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
Forward voltage	$I_F=16A, T_j=25^{\circ}C$	V_F	-	1.45	1.8	V
	$I_F=16A, T_j=175^{\circ}C$		-	1.75	3.0	
Reverse current	$V_R=650V, T_j=25^{\circ}C$	I_R	-	4	20	μA
	$V_R=650V, T_j=175^{\circ}C$		-	40	200	
Total capacitance	$V_R=0V, f=1MHz$	C	-	860	-	pF
	$V_R=200V, f=1MHz$		-	85	-	
	$V_R=400V, f=1MHz$		-	60	-	
Total capacitance charge	$V_R=400V, T_j=25^{\circ}C$	Q_C	-	41	-	nC
Capacitance stored energy	$V_R=400V$	E_C	-	8.2	-	μJ

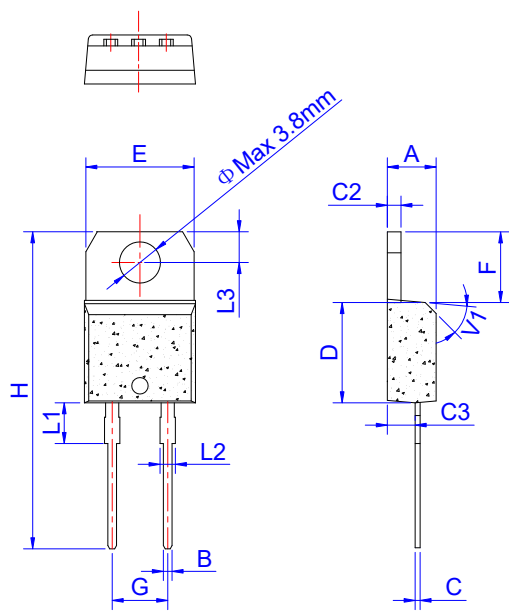
THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	1.6	$^{\circ}C/W$

ORDERING INFORMATION

J	CD	16	A	065	A
JieJie Microelectronics Co., Ltd	SiC Schottky Diode	$I_{F(AV)}=16A$	A: TO-220A-2L(Ins)	$V_{RRM}:650V$	Version A

PACKAGE MECHANICAL DATA



TO-220A-2L Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		5.08		0.1		
H	28.0		29.8	1.102		1.173
L1		3.75		0.148		
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°		45°		

CHARACTERITICS CURVE

FIG.1: Forward characteristics

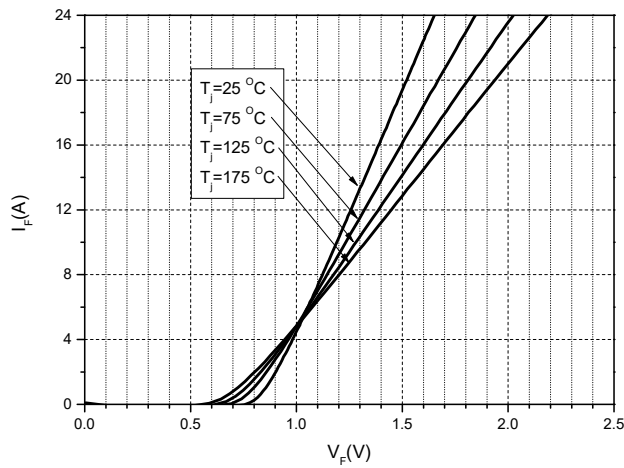
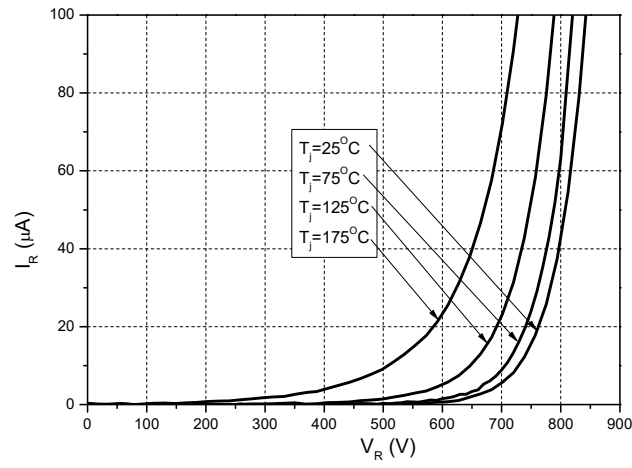


FIG.2: Reverse characteristics



CHARACTERISTICS CURVE

FIG.3: Capacitance vs. reverse voltage

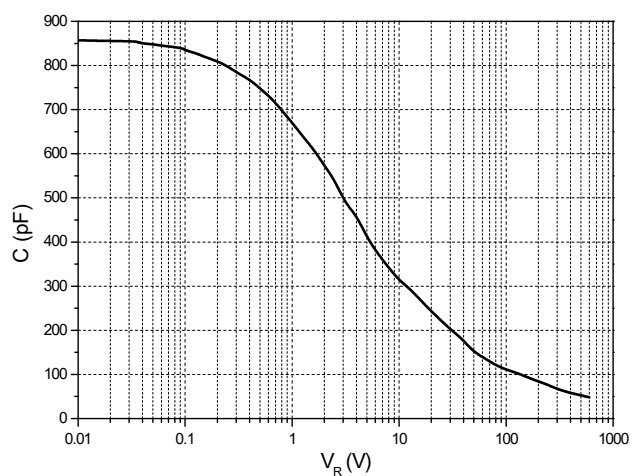


FIG.4: Transient thermal impedance

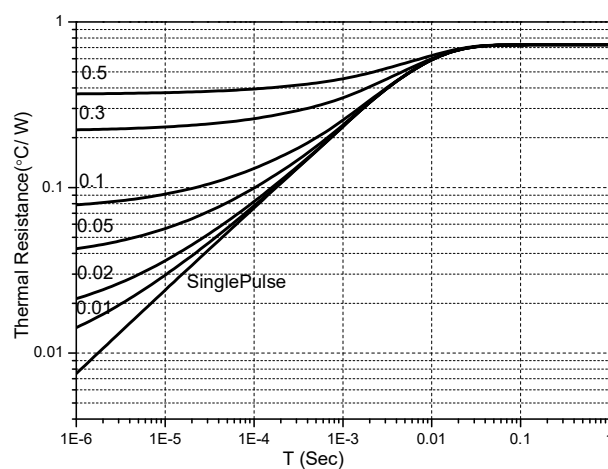


FIG.5: Capacitance charge vs. reverse voltage

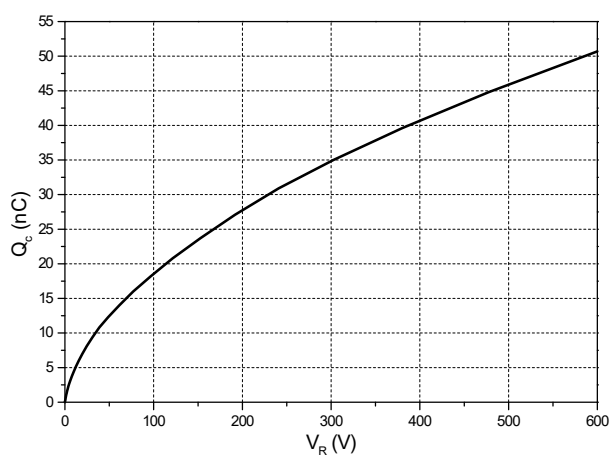


FIG.6: Capacitance stored energy

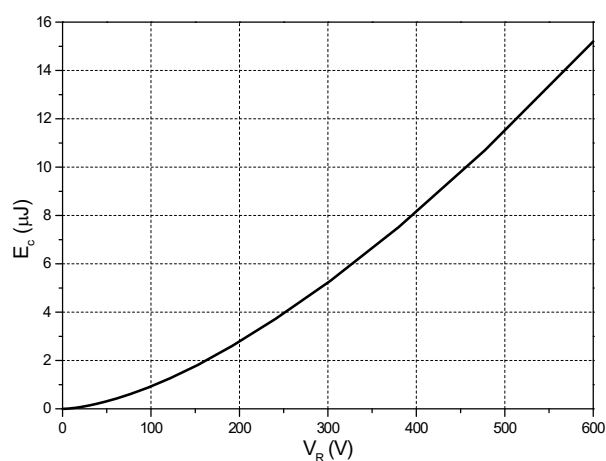


FIG.7: Power derating

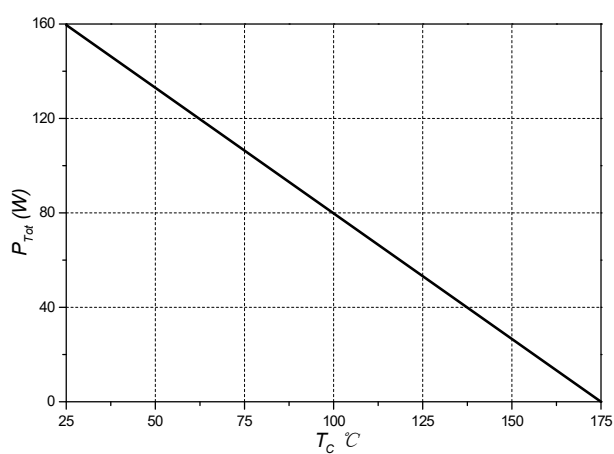
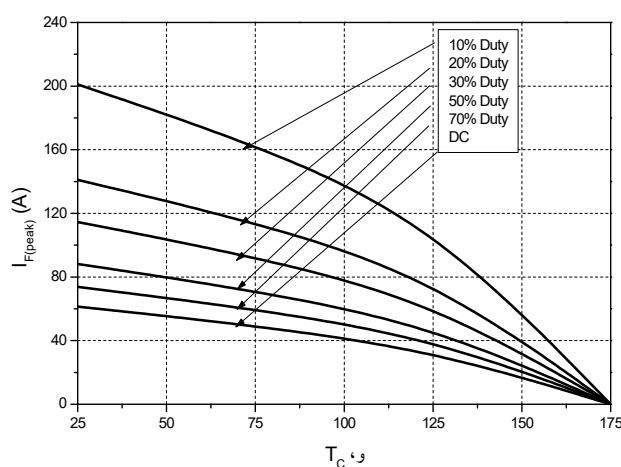


FIG.8: Current derating



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